R3000 200mA 3.0kV

High Voltage Silicon Rectifier Diode

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Low leakage.
2. Low forward voltage drop.
3. High current capability.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Rectifier for high voltage power supply.
2. High voltage transformer rectifier.
3. Doubler rectifier circuit.
4. Accelerator power supply.

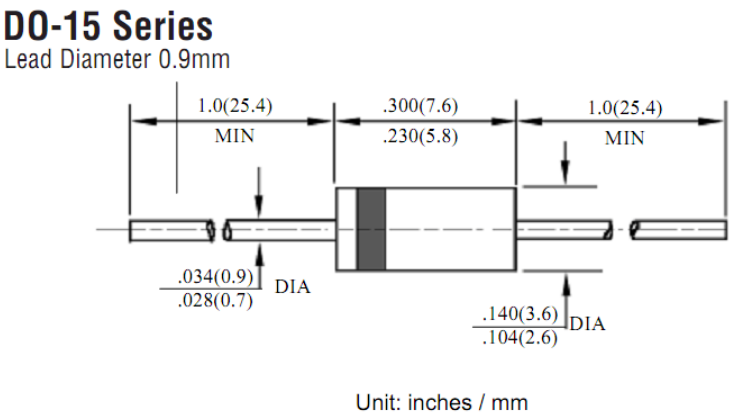
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.4 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) **HVGT NAME: DO-15**



MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C	3000	V
Non-Repetitive Peak Renerse Voltage	V_{RSM}	T_A=25°C	2100	V
Average Forward Current Maximum	I_{FAVM}	T_A=50°C	200	mA
		T_{OIL}=55°C	--	A
Non-Repetitive Forward Surge Current	I_{FSM}	T_A=25°C; 60Hz Half-Sine Wave; 8.3mS	30	A
Junction Temperature	T_J		150	°C
Allowable Operation Case Temperature	Tc		-65~+150	°C
Storage Temperature	T_{STG}		-65~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	4.0	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	5.0	uA
	I_{R2}	at 100°C; at V_{RRM}	40	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	--	nS
Junction Capacitance	C_J	at 25°C; V_R=4.0V; f=1MHz	30	pF

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Fig 1

Forward Current Derating Curve

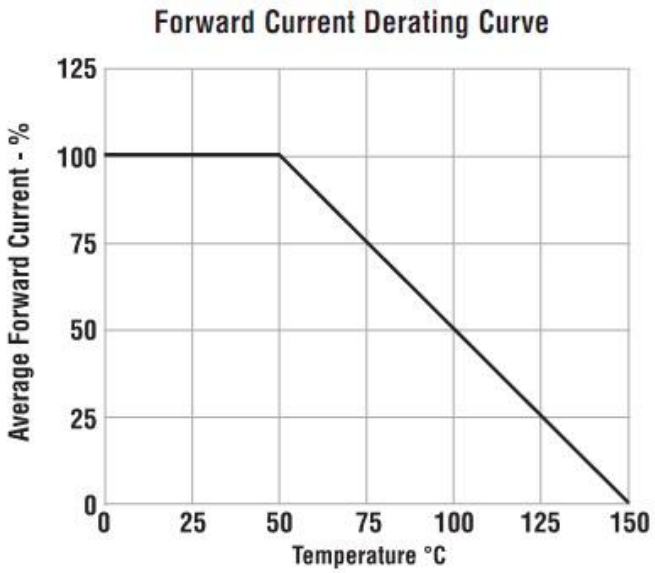
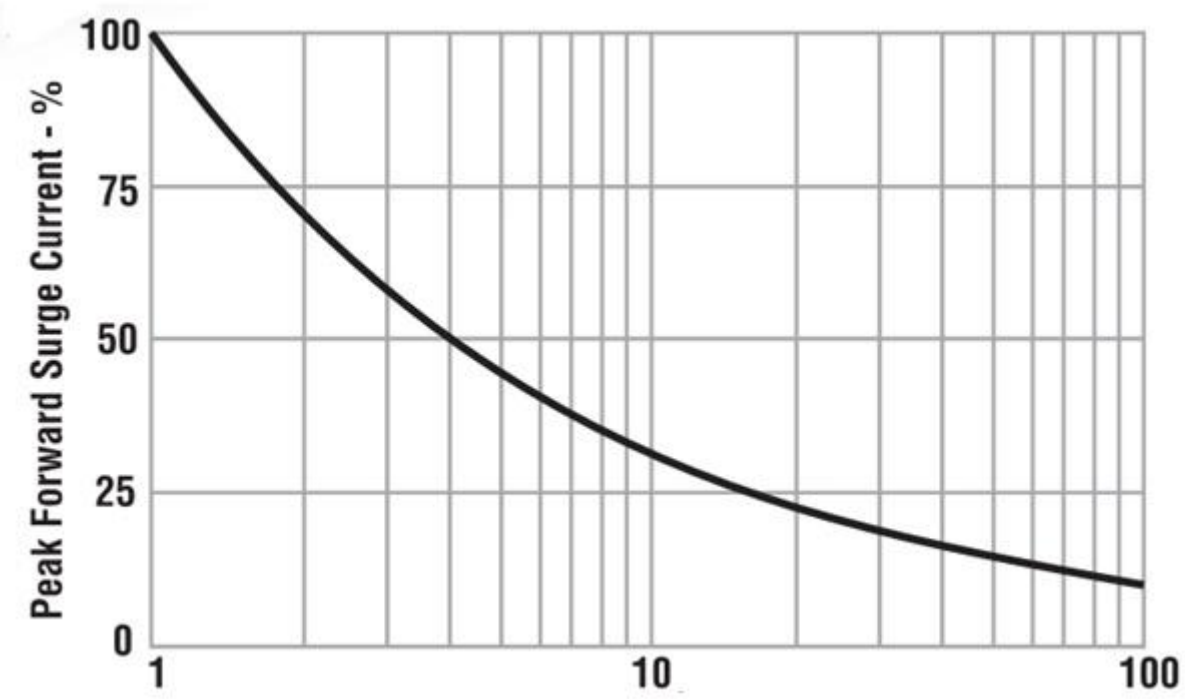


Fig 2

Non-Repetitive Surge Current



Marking	Type	Code	Cathode Mark
	R3000	R3000 HVGT	

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